

Silicon PNP Power Transistors

2SB812

DESCRIPTION

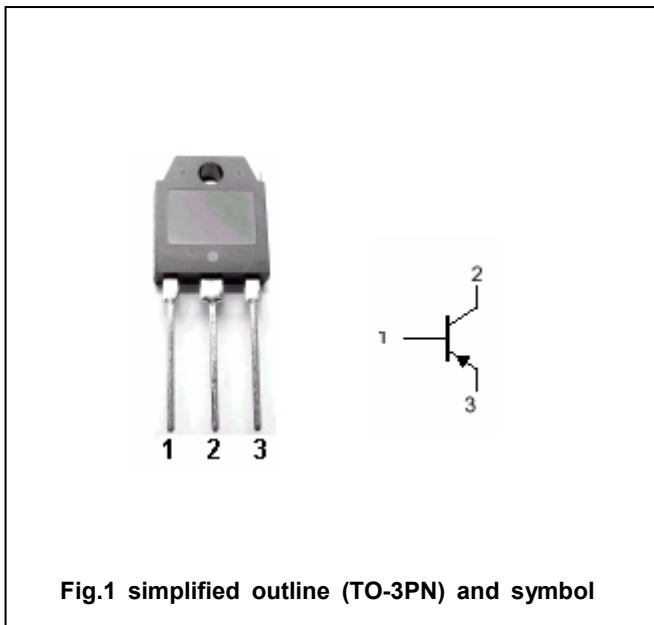
- With TO-3PN package
- Wide area of safe operation
- Low collector saturation voltage

APPLICATIONS

- For audio frequency output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current (DC)		-4	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	60	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-40~150	$^\circ\text{C}$

Silicon PNP Power Transistors**2SB812****CHARACTERISTICS****T_j=25℃ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA ; I_B=0$	-60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-1mA ; I_E=0$	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1mA ; I_C=0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3A ; I_B=-0.3A$			-1.5	V
V_{BE}	Base-emitter on voltage	$I_C=-1A ; V_{CE}=-5V$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-60V ; I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6V ; I_C=0$			-0.1	mA
h_{FE}	DC current gain	$I_C=-1A ; V_{CE}=-4V$	40		250	

Silicon PNP Power Transistors

2SB812

PACKAGE OUTLINE

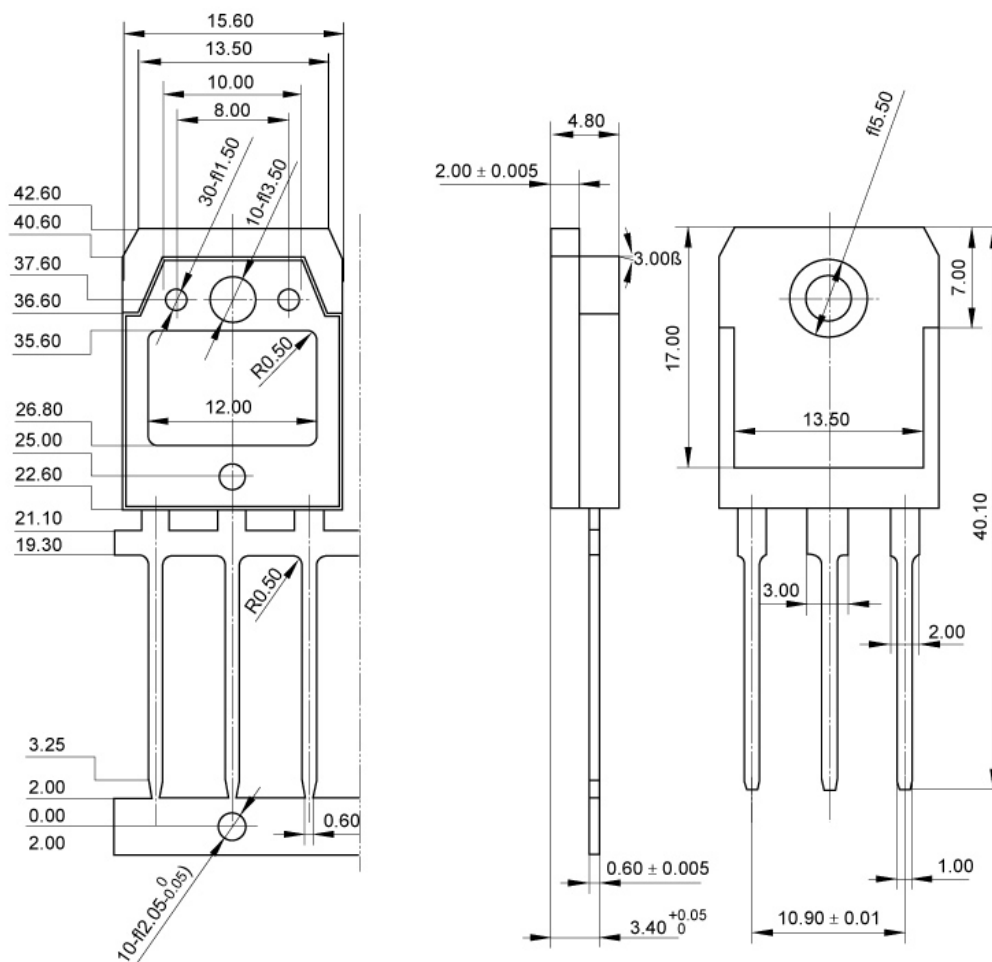


Fig.2 outline dimensions